

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claims 1-19 (canceled).

Claim 20 (previously presented): A method for forming a thick film pattern, comprising the steps of:

applying to a support a photosensitive paste including an inorganic powder, a photosensitive monomer, a photopolymerization initiator, and a polymer, wherein a ratio of the photosensitive monomer to a total amount of the photosensitive monomer and the polymer satisfies the condition represented by the following Formula:

photosensitive monomer/(photosensitive monomer + polymer)  $\geq$  0.86,  
so as to form a photosensitive paste film;  
subjecting the photosensitive paste film to an exposure treatment; and  
developing the photosensitive paste film subjected to the exposure treatment so as to form a thick film pattern.

Claim 21 (currently amended): The method for forming a thick film pattern according to Claim 19~~20~~, wherein the contents of the inorganic powder, the photosensitive monomer, and the photopolymerization initiator constituting the photosensitive paste are within the following ranges:

inorganic powder: about 60 to about 90 percent by weight;  
photosensitive monomer: about 5 to about 39 percent by weight; and  
photopolymerization initiator: about 1 to about 10 percent by weight.

Claim 22 (currently amended): The method for forming a thick film pattern

according to Claim ~~49~~20, wherein the photosensitive paste includes a photosensitive monomer having a double bond concentration within the range of about 8 mmol/g to about 11 mmol/g.

Claim 23 (currently amended): The method for forming a thick film pattern according to Claim ~~49~~20, wherein the photosensitive paste includes a photosensitive monomer having an ethylene oxide structure with a degree of polymerization of about 3 or less.

Claim 24 (currently amended): The method for forming a thick film pattern according to Claim ~~49~~20, wherein the photosensitive paste comprises an ultraviolet absorber.

Claim 25 (currently amended): The method for forming a thick film pattern according to Claim ~~49~~20, wherein the photosensitive paste comprises a solvent in a proportion of about 5 percent by weight or less.

Claim 26 (currently amended): The method for forming a thick film pattern according to Claim ~~49~~20, wherein development is conducted by using an organic solvent in the development step.

Claim 27 (currently amended): The method for forming a thick film pattern according to Claim ~~49~~20, wherein the exposure treatment is conducted while the photosensitive paste film and a photomask are arranged to be kept from contacting with each other in the exposure step.

Claim 28 (currently amended): The method for forming a thick film pattern according to Claim ~~49~~20, wherein the photosensitive paste is subjected to the exposure

treatment without using a photomask in the exposure step.

Claim 29 (currently amended): A method for manufacturing an electronic component, comprising the steps of:

forming a thick film pattern by the method according to Claim ~~49~~20; and  
firing the resulting thick film pattern.

Claim 30 (canceled).

Claim 31 (previously presented): A photolithography photosensitive paste comprising:

an inorganic powder;  
a photosensitive monomer;  
a photopolymerization initiator; and  
a polymer; wherein

a ratio of the photosensitive monomer to a total amount of the photosensitive monomer and the polymer satisfies the condition represented by the following Formula:  
$$\text{photosensitive monomer}/(\text{photosensitive monomer} + \text{polymer}) \geq 0.86.$$

Claim 32 (currently amended): The photolithography photosensitive paste according to Claim ~~30~~31, wherein the contents of the inorganic powder, the photosensitive monomer, and the photopolymerization initiator are within the following ranges:

inorganic powder: about 60 to about 90 percent by weight,  
photosensitive monomer: about 5 to about 39 percent by weight, and  
photopolymerization initiator: about 1 to about 10 percent by weight.

Claim 33 (currently amended): The photolithography photosensitive paste

according to Claim ~~30~~31, wherein the photosensitive monomer is a photosensitive monomer having a double bond concentration within the range of about 8 mmol/g to about 11 mmol/g.

Claim 34 (currently amended): The photolithography photosensitive paste according to Claim ~~30~~31, wherein the photosensitive monomer is a photosensitive monomer having an ethylene oxide structure with a degree of polymerization of about 3 or less.

Claim 35 (currently amended): The photolithography photosensitive paste according to Claim ~~30~~31, further comprising an ultraviolet absorber.

Claim 36 (currently amended): The photolithography photosensitive paste according to Claim ~~30~~31, further comprising a solvent in a proportion of about 5 percent by weight or less.